

TLV713

ポータブル機器向け、コンデンサ不要、フォールドバック電流制限付き 150mA 低ドロップアウト (LDO) レギュレータ

1 特長

- コンデンサあり/なしのどちらでも安定した動作
- フォールドバック過電流保護
- パッケージ
 - 1mm x 1mm の 4 ピン X2SON
 - 5ピンSOT-23
- 非常に低いドロップアウト: 150mAで230mV
- 精度: 1%
- 低い I_Q : 50 μ A
- 入力電圧範囲: 1.4V~5.5V
- 固定出力電圧で利用可能: 1V~3.3V
- 高いPSRR: 1kHzにおいて65dB
- アクティブ出力放電(Pバージョンのみ)

2 アプリケーション

- PDAおよびバッテリー駆動の携帯機器
- MP3プレーヤーや他のハンドヘルド製品
- WLANおよび他のPCアドオン・カード

3 概要

TLV713 シリーズの LDO (低ドロップアウト) リニア・レギュレータはラインおよび負荷過渡性能が非常に優れた低静止電流 LDO であり、電力の制約が厳しいアプリケーション用に設計されています。これらのデバイスの精度は 1% (標準値) です。

TLV713 シリーズのデバイスは、出力コンデンサなしで安定するように設計されています。出力コンデンサが必要ないため、非常に小型のソリューションが可能です。しかし、出力コンデンサを使用した場合も、TLV713 シリーズは任意の出力コンデンサで安定します。

また TLV713 は、デバイスの電源投入およびイネーブル時に突入電流の制御も行います。TLV713 は定義済みの上限値に入力電流を制限し、入力電源から大電流が流れ込むことを防止します。この機能は、バッテリーで動作するデバイスでは特に重要です。

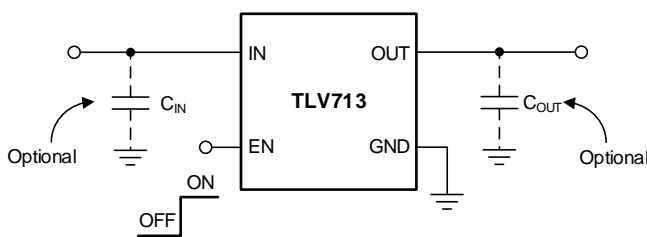
TLV713 シリーズは、標準の DQN および DBV パッケージで供給されます。TLV713P は、出力負荷をすばやく放電するためのアクティブ・プルダウン回路を備えています。

製品情報⁽¹⁾

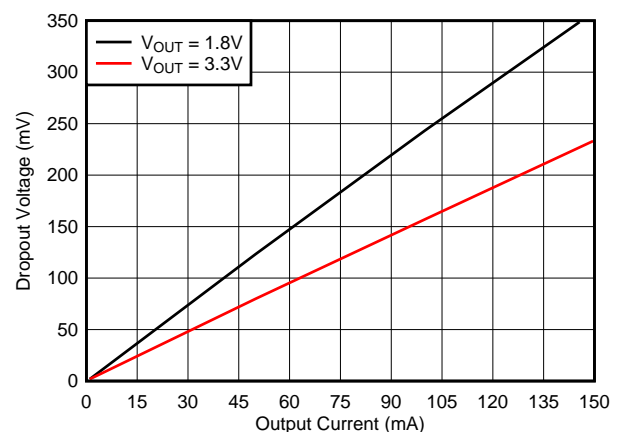
型番	パッケージ	本体サイズ
TLV713	X2SON (4)	1.00mmx1.00mm
	SOT-23 (5)	2.90mmx1.60mm

(1) 提供されているすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。

代表的なアプリケーション回路



ドロップアウト電圧と出力電流との関係



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4 改訂履歴

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Revision E (March 2015) から Revision F に変更	Page
• Added last sentence to <i>Undervoltage Lockout (UVLO)</i> section	13
• Added <i>UVLO Circuit Limitation</i> section	16

Revision D (July 2013) から Revision E に変更	Page
• 新規セクションを追加、既存のセクションを移動、最新のデータシート標準に合わせてフォーマットを変更.....	1
• 「特長」の箇条書きにデバイスのパッケージ・オプションを変更.....	1
• 表紙の図 変更	1
• Changed Pin Configuration and Functions section; updated table format	5
• Changed Absolute Maximum Ratings table conditions	6
• Changed <i>Output voltage range</i> and <i>Junction temperature range</i> parameter maximum specifications in Absolute Maximum Ratings table	6
• Added <i>ESD Ratings</i> table, <i>Feature Description</i> section, <i>Device Functional Modes</i> , <i>Application and Implementation</i> section, <i>Power Supply Recommendations</i> section, <i>Layout</i> section, <i>Device and Documentation Support</i> section, and <i>Mechanical, Packaging, and Orderable Information</i> section	6
• Corrected DBV data in Thermal Information table	6
• Changed conditions of Electrical Characteristics table: changed V_{IN} to $V_{IN(nom)}$; changed T_A to T_J ; corrected operating temperature range	7
• Changed T_A to T_J and 85°C to 125°C throughout Electrical Characteristics table	7
• Added test conditions for line regulation parameter	7
• Changed V_{DO} parameter in Electrical Characteristics table: all rows changed	7
• Changed V_n parameter typical specification in Electrical Characteristics table	7
• Deleted T_J parameter from Electrical Characteristics table	7
• Added T_J condition to I_{LIM} parameter in Electrical Characteristics table for clarification	7
• Changed Typical Characteristics conditions.....	8
• Changed Figure 1 through Figure 11 in Typical Characteristics to show improved performance definition	8
• Added new Figure 3	8

• Changed Figure 4	8
• Changed Figure 5	8
• Changed Figure 9 graph and figure title.....	8
• Added new Figure 10	8
• Changed Figure 12 ; corrected notation on axis titles to show units per graph division (units/div)	8
• Changed Figure 13 ; corrected notation on axis titles to show units per graph division (units/div)	9
• Changed Figure 14 ; corrected notation on axis titles to show units per graph division (units/div)	9
• Changed Figure 15 ; corrected notation on axis titles to show units per graph division (units/div)	9
• Changed Figure 17 ; corrected notation on axis titles to show units per graph division (units/div)	9
• Changed Figure 19 ; corrected notation on axis titles to show units per graph division (units/div)	10
• Changed Figure 21 ; corrected notation on axis titles to show units per graph division (units/div)	10
• Changed Figure 22 ; corrected notation on axis titles to show units per graph division (units/div)	10
• Changed Figure 23 ; corrected notation on axis titles to show units per graph division (units/div)	10
• Changed Shutdown section: clarified description	13
• Changed Foldback Current Limit section: adjusted flow and clarified description	14
• Changed paragraph 1 of Thermal Protection	14
• Changed Table 2	17
• 「注文情報」を「デバイスの項目表記」セクションに移動	21

Revision C (July 2013) から Revision D に変更
Page

• ドキュメントのステータスを「混在ステータス」から「量産データ」に変更.....	1
• ドキュメントから DPW パッケージを削除	1
• 「概要」セクションの最後の文から DPW パッケージへの言及を削除	1
• 表紙のグラフィックから DPW のピン配置の図を削除.....	1
• ページ 1 のグラフィックの脚注 削除	1
• Deleted DPW pinout drawing from Pin Configurations section	5
• Deleted reference to DPW package from Pin Descriptions table.....	5
• Deleted DPW data from Thermal Information table	6
• 削除「注文情報」表の脚注 3	21

Revision B (December 2012) から Revision C に変更
Page

• 「特長」の最後の箇条書き項目 変更	1
• 代表的なアプリケーション回路 追加	1
• Changed last two rows of the V_{DO} parameter in the Electrical Characteristics table	7

Revision A (October 2012) から Revision B に変更
Page

• ページ 1 のグラフィックの脚注 変更	1
• Added DBV data to Thermal Information table.....	6
• 変更「注文情報」表の脚注 3	21

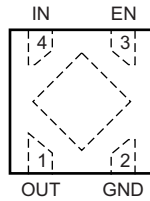
2012年9月発行のものから更新
Page

• 「特長」の箇条書きの順序を変更	1
• 「特長」の 4 番目の箇条書き項目にドロップアウト範囲を 変更	1
• 「特長」の「パッケージ」および「固定出力電圧」箇条書き項目 変更.....	1

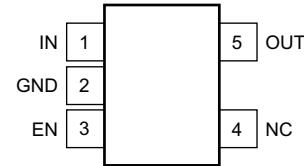
• 「概要」セクションの 2 番目と 3 番目の段落 追加	1
• DQN ピン配置の図を更新	1
• Changed DQN pinout caption in Pin Configurations section.....	5
• Changed 1.2 V to 0.9 V in description of EN pin in Pin Descriptions table.....	5
• Changed DQN header row in Thermal Information table	6
• Changed V_{OUT} maximum specification in Electrical Characteristics table	7
• Combined all V_{DO} rows together in Electrical Characteristics table	7
• Changed V_{DO} specifications in Electrical Characteristics table	7
• Changed I_{SHDN} test conditions in Electrical Characteristics table.....	7
• Changed Typical Characteristics conditions.....	8
• Added curves.....	8
• Changed junction temperature range in second paragraph of <i>Overview</i> section	12
• Updated Figure 24	12
• Deleted third paragraph from <i>Thermal Information</i> section.....	14
• Changed second paragraph of <i>Input and Output Capacitor Considerations</i> section.....	16
• Deleted curve reference from <i>Dropout Voltage</i> section	16

5 Pin Configurations and Functions

**DQN Package
4-Pin X2SON
Top View**



**DBV Package
5-Pin SOT-23
Top View**



Pin Functions

NAME	PIN NO.		I/O	DESCRIPTION
	X2SON	SOT-23		
EN	3	3	I	Enable pin. Driving EN over 0.9 V turns on the regulator. Driving EN below 0.4 V puts the regulator into shutdown mode.
GND	2	2	—	Ground pin
IN	4	1	I	Input pin. A small capacitor is recommended from this pin to ground. See the Input and Output Capacitor Considerations section in the Feature Description for more details.
NC	—	4	—	No internal connection
OUT	1	5	O	Regulated output voltage pin. For best transient response, a small 1- μ F ceramic capacitor is recommended from this pin to ground. See the Input and Output Capacitor Considerations section in the Feature Description for more details.
Thermal pad	—	—	—	The thermal pad is electrically connected to the GND node. Connect to the GND plane for improved thermal performance.

6 Specifications

6.1 Absolute Maximum Ratings

Over operating junction temperature range ($T_J = 25^\circ\text{C}$), unless otherwise noted. All voltages are with respect to GND.⁽¹⁾

		MIN	MAX	UNIT
Voltage	Input, V_{IN}	-0.3	6	V
	Enable, V_{EN}	-0.3	$V_{IN} + 0.3$	
	Output, V_{OUT}	-0.3	3.6	
Current	Maximum output, $I_{OUT(max)}$	Internally limited		
Output short-circuit duration		Indefinite		
Total power dissipation	Continuous, $P_{D(tot)}$	See Thermal Information		
Temperature	Storage, T_{stg}	-55	150	$^\circ\text{C}$
	Junction, T_J	-55	125	$^\circ\text{C}$

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	± 2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	± 500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
 (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating junction temperature range (unless otherwise noted).

		MIN	NOM	MAX	UNIT
V_{IN}	Input voltage	1.4		5.5	V
V_{EN}	Enable range	0		V_{IN}	V
I_{OUT}	Output current	0		150	mA
C_{IN}	Input capacitor	0	1		μF
C_{OUT}	Output capacitor	0	0.1	100	μF
T_J	Operating junction temperature range	-40		125	$^\circ\text{C}$

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TLV713, TLV713P		UNIT
		DQN (X2SON)	DBV (SOT23)	
		4 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	255.8	249	$^\circ\text{C}/\text{W}$
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	159.3	172.7	$^\circ\text{C}/\text{W}$
$R_{\theta JB}$	Junction-to-board thermal resistance	208.2	76.7	$^\circ\text{C}/\text{W}$
ψ_{JT}	Junction-to-top characterization parameter	16.2	49.7	$^\circ\text{C}/\text{W}$
ψ_{JB}	Junction-to-board characterization parameter	208.1	75.8	$^\circ\text{C}/\text{W}$
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	148.6	n/a	$^\circ\text{C}/\text{W}$

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics application report](#).

6.5 Electrical Characteristics

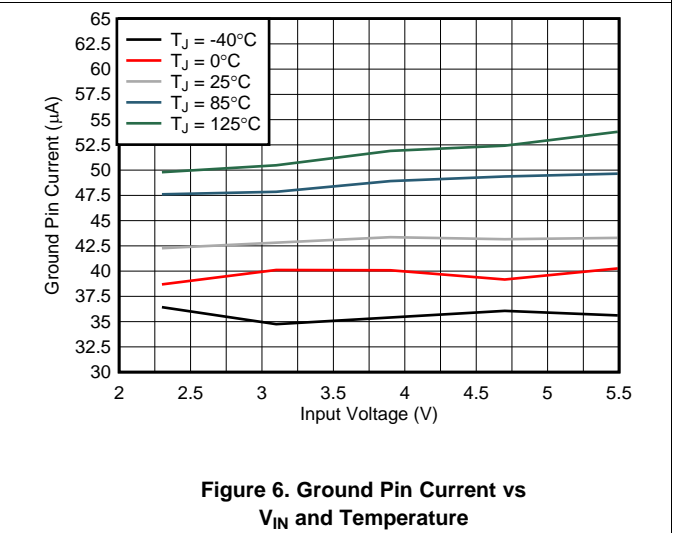
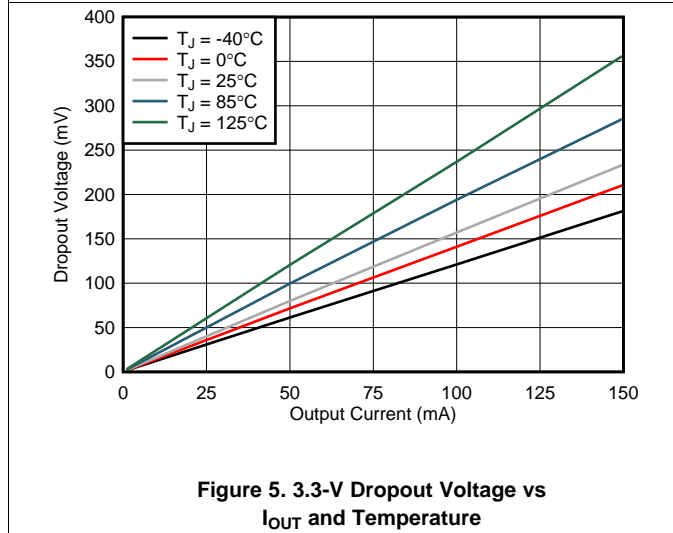
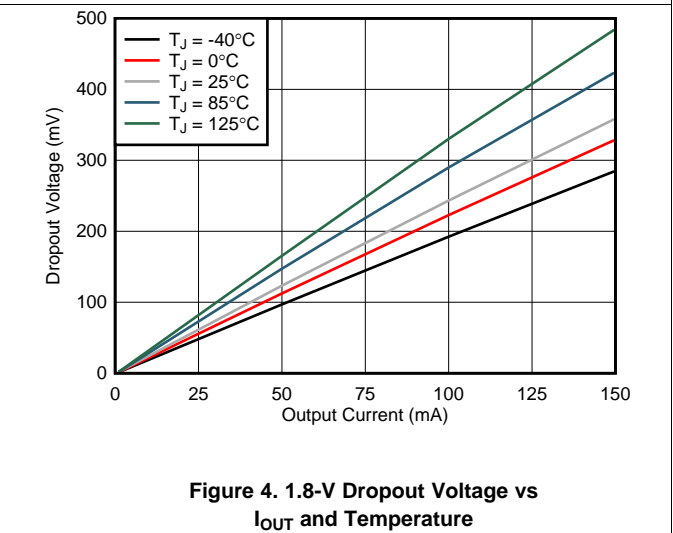
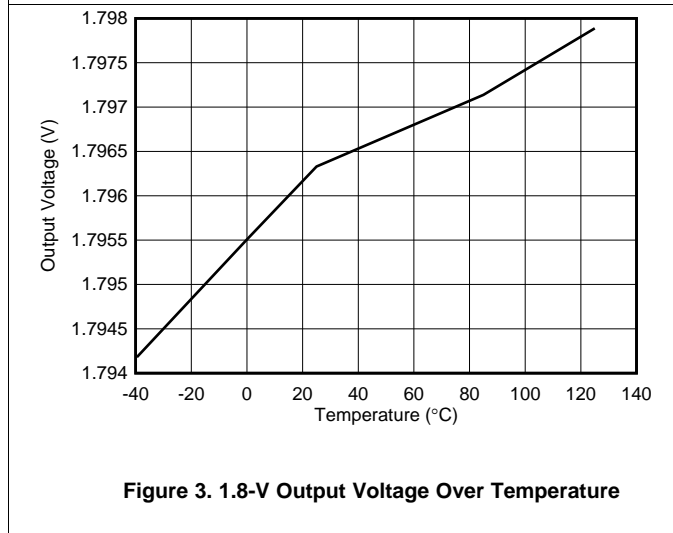
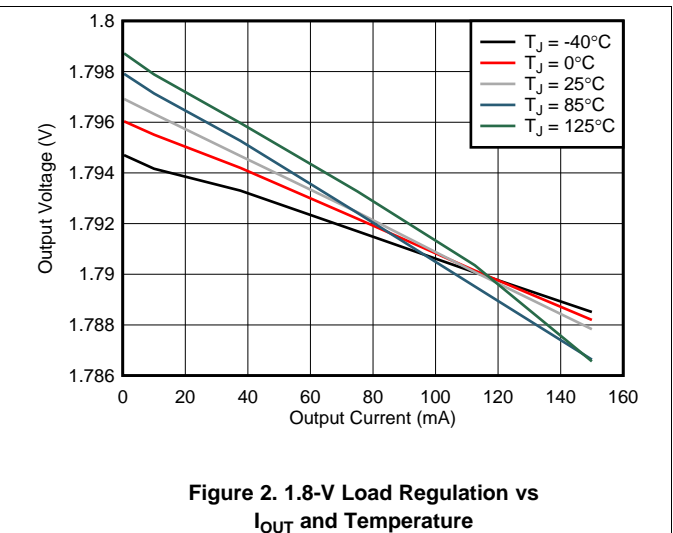
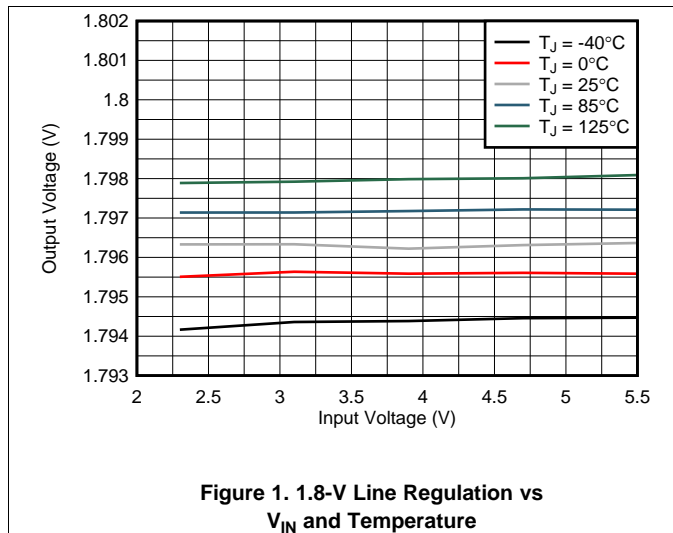
Over operating temperature range ($T_J = -40^\circ\text{C}$ to 125°C), $V_{IN(nom)} = V_{OUT(nom)} + 0.5\text{ V}$ or $V_{IN(nom)} = 2\text{ V}$ (whichever is greater), $I_{OUT} = 1\text{ mA}$, $V_{EN} = V_{IN}$, and $C_{OUT} = 0.47\text{ }\mu\text{F}$, unless otherwise noted. Typical values are at $T_J = 25^\circ\text{C}$.

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{IN}	Input voltage range			1.4		5.5	V
V_{OUT}	Output voltage range			1		3.3	V
	DC output accuracy	$V_{OUT} \geq 1.8\text{ V}$, $T_J = 25^\circ\text{C}$		-1%		1%	
		$V_{OUT} < 1.8\text{ V}$, $T_J = 25^\circ\text{C}$		-20		20	mV
		$V_{OUT} \geq 1.2\text{ V}$, $-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$		-1.5%		1.5%	
		$V_{OUT} < 1.2\text{ V}$, $-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$		-50		50	mV
$\Delta V_{OUT(\Delta V_{IN})}$	Line regulation	Max $\{V_{OUT(nom)} + 0.5\text{ V}, V_{IN} = 2.0\text{ V}\} \leq V_{IN} \leq 5.5\text{ V}$			1	5	mV
$\Delta V_{OUT(\Delta I_{OUT})}$	Load regulation	$0\text{ mA} \leq I_{OUT} \leq 150\text{ mA}$			10	30	mV
V_{DO}	Dropout voltage	$V_{OUT} = 0.98 \times V_{OUT(nom)}$, $T_J = -40^\circ\text{C}$ to 85°C	$1\text{ V} \leq V_{OUT} < 1.8\text{ V}$, $I_{OUT} = 150\text{ mA}$		600	900	mV
			$V_{OUT} = 1.1\text{ V}$, $I_{OUT} = 100\text{ mA}$		470	600	
			$1.8\text{ V} \leq V_{OUT} < 2.1\text{ V}$, $I_{OUT} = 30\text{ mA}$		70		
			$1.8\text{ V} \leq V_{OUT} < 2.1\text{ V}$, $I_{OUT} = 150\text{ mA}$		350	575	
			$2.1\text{ V} \leq V_{OUT} < 2.5\text{ V}$, $I_{OUT} = 30\text{ mA}$		90		
			$2.1\text{ V} \leq V_{OUT} < 2.5\text{ V}$, $I_{OUT} = 150\text{ mA}$		290	481	
			$2.5\text{ V} \leq V_{OUT} < 3\text{ V}$, $I_{OUT} = 30\text{ mA}$		50		
			$2.5\text{ V} \leq V_{OUT} < 3\text{ V}$, $I_{OUT} = 150\text{ mA}$		246	445	
		$V_{OUT} = 0.98 \times V_{OUT(nom)}$, $T_J = -40^\circ\text{C}$ to 125°C	$3\text{ V} \leq V_{OUT} < 3.6\text{ V}$, $I_{OUT} = 30\text{ mA}$		46		
			$3\text{ V} \leq V_{OUT} < 3.6\text{ V}$, $I_{OUT} = 150\text{ mA}$		230	420	
			$1\text{ V} \leq V_{OUT} < 1.8\text{ V}$, $I_{OUT} = 150\text{ mA}$		600	1020	
			$V_{OUT} = 1.1\text{ V}$, $I_{OUT} = 100\text{ mA}$		470	720	
			$1.8\text{ V} \leq V_{OUT} < 2.1\text{ V}$, $I_{OUT} = 150\text{ mA}$		350	695	
			$2.1\text{ V} \leq V_{OUT} < 2.5\text{ V}$, $I_{OUT} = 150\text{ mA}$		290	601	
			$2.5\text{ V} \leq V_{OUT} < 3\text{ V}$, $I_{OUT} = 150\text{ mA}$		246	565	
			$3\text{ V} \leq V_{OUT} < 3.6\text{ V}$, $I_{OUT} = 150\text{ mA}$		230	540	
I_{GND}	Ground pin current	$I_{OUT} = 0\text{ mA}$			50	75	μA
$I_{SHUTDOWN}$	Shutdown current	$V_{EN} \leq 0.4\text{ V}$, $2.0\text{ V} \leq V_{IN} \leq 5.5\text{ V}$, $T_J = 25^\circ\text{C}$			0.1	1	μA
PSRR	Power-supply rejection ratio	$V_{IN} = 3.3\text{ V}$, $V_{OUT} = 2.8\text{ V}$, $I_{OUT} = 30\text{ mA}$	$f = 100\text{ Hz}$		70		dB
			$f = 10\text{ kHz}$		55		
			$f = 1\text{ MHz}$		55		
V_n	Output noise voltage	BW = 100 Hz to 100 kHz, $V_{IN} = 2.3\text{ V}$, $V_{OUT} = 1.8\text{ V}$, $I_{OUT} = 10\text{ mA}$			73		μV_{RMS}
t_{STR}	Start-up time ⁽¹⁾	$C_{OUT} = 1.0\text{ }\mu\text{F}$, $I_{OUT} = 150\text{ mA}$			100		μs
V_{HI}	Enable high (enabled)			0.9		V_{IN}	V
V_{LO}	Enable low (disabled)			0		0.4	V
I_{EN}	EN pin current	EN = 5.5 V			0.01		μA
$R_{PULLDOWN}$	Pulldown resistor (TLV713P only)	$V_{IN} = 4\text{ V}$			120		Ω
I_{LIM}	Output current limit	$V_{IN} = 3.8\text{ V}$, $V_{OUT} = 3.3\text{ V}$, $T_J = -40$ to 85°C		180			mA
		$V_{IN} = 2.25\text{ V}$, $V_{OUT} = 1.8\text{ V}$, $T_J = -40$ to 85°C		180			
		$V_{IN} = 2.0\text{ V}$, $V_{OUT} = 1.2\text{ V}$, $T_J = -40$ to 85°C		180			
I_{SC}	Short-circuit current	$V_{OUT} = 0\text{ V}$			40		mA
T_{SD}	Thermal shutdown	Shutdown, temperature increasing			158		$^\circ\text{C}$
		Reset, temperature decreasing			140		

(1) Start-up time is the time from EN assertion to $(0.98 \times V_{OUT(nom)})$.

6.6 Typical Characteristics

Over operating temperature range ($T_J = -40^{\circ}\text{C}$ to 125°C), $V_{IN} = V_{OUT(nom)} + 0.5\text{ V}$ or 2.0 V (whichever is greater), $I_{OUT} = 10\text{ mA}$, $V_{EN} = V_{IN}$, $C_{OUT} = 1\text{ }\mu\text{F}$, and $V_{OUT(nom)} = 1.8\text{ V}$, unless otherwise noted. Typical values are at $T_J = 25^{\circ}\text{C}$.



Typical Characteristics (continued)

Over operating temperature range ($T_J = -40^{\circ}\text{C}$ to 125°C), $V_{IN} = V_{OUT(nom)} + 0.5\text{ V}$ or 2.0 V (whichever is greater), $I_{OUT} = 10\text{ mA}$, $V_{EN} = V_{IN}$, $C_{OUT} = 1\text{ }\mu\text{F}$, and $V_{OUT(nom)} = 1.8\text{ V}$, unless otherwise noted. Typical values are at $T_J = 25^{\circ}\text{C}$.

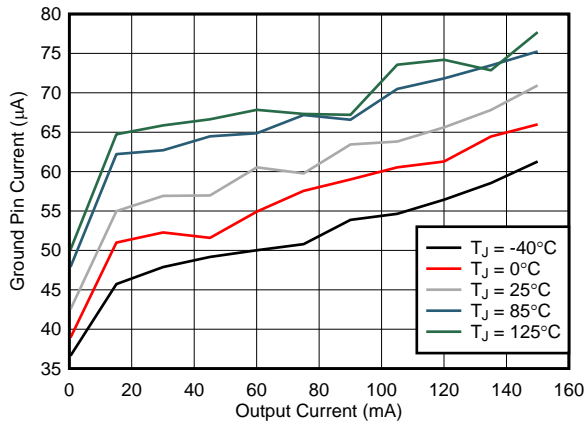


Figure 7. Ground Pin Current vs I_{OUT} and Temperature

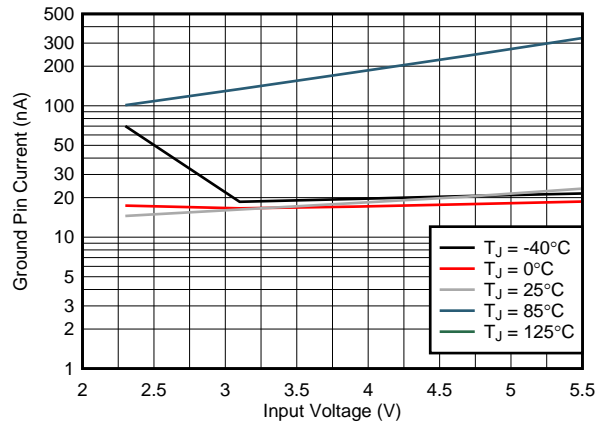


Figure 8. Shutdown Current vs V_{IN} and Temperature

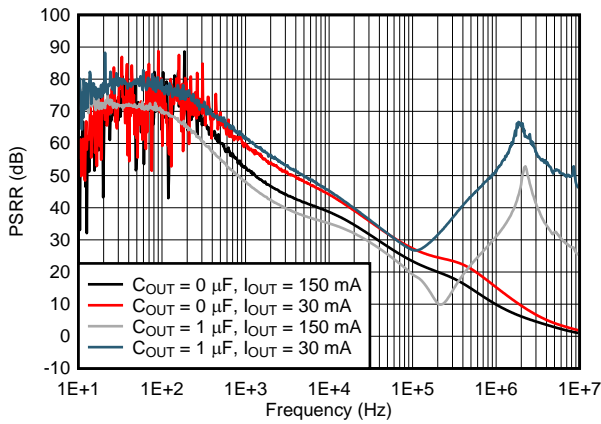


Figure 9. Power-Supply Rejection Ratio Over C_{OUT}

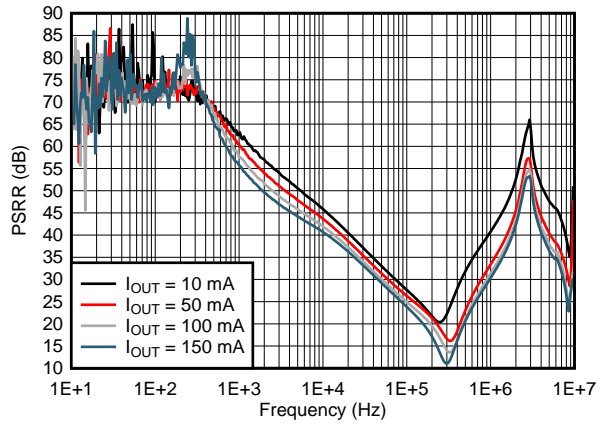


Figure 10. Power-Supply Rejection Ratio Over I_{OUT}

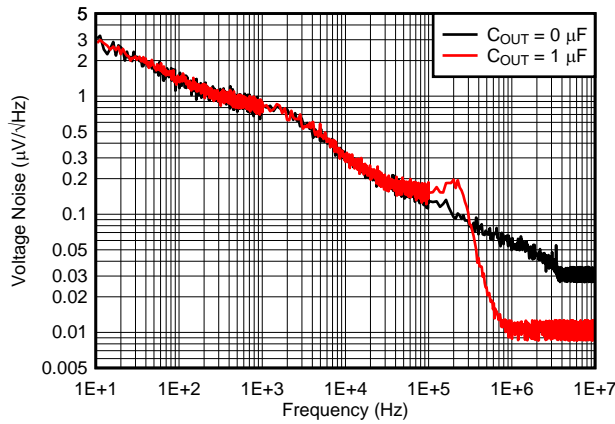


Figure 11. Output Spectral Noise Density

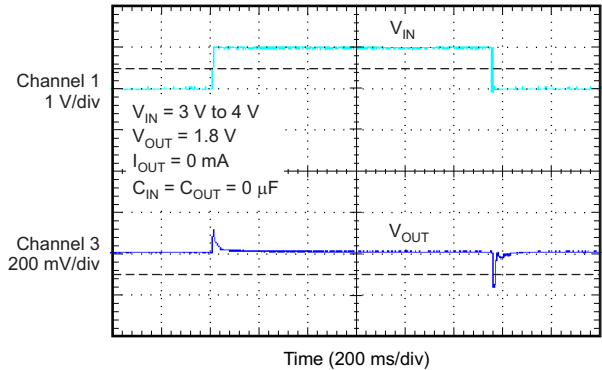
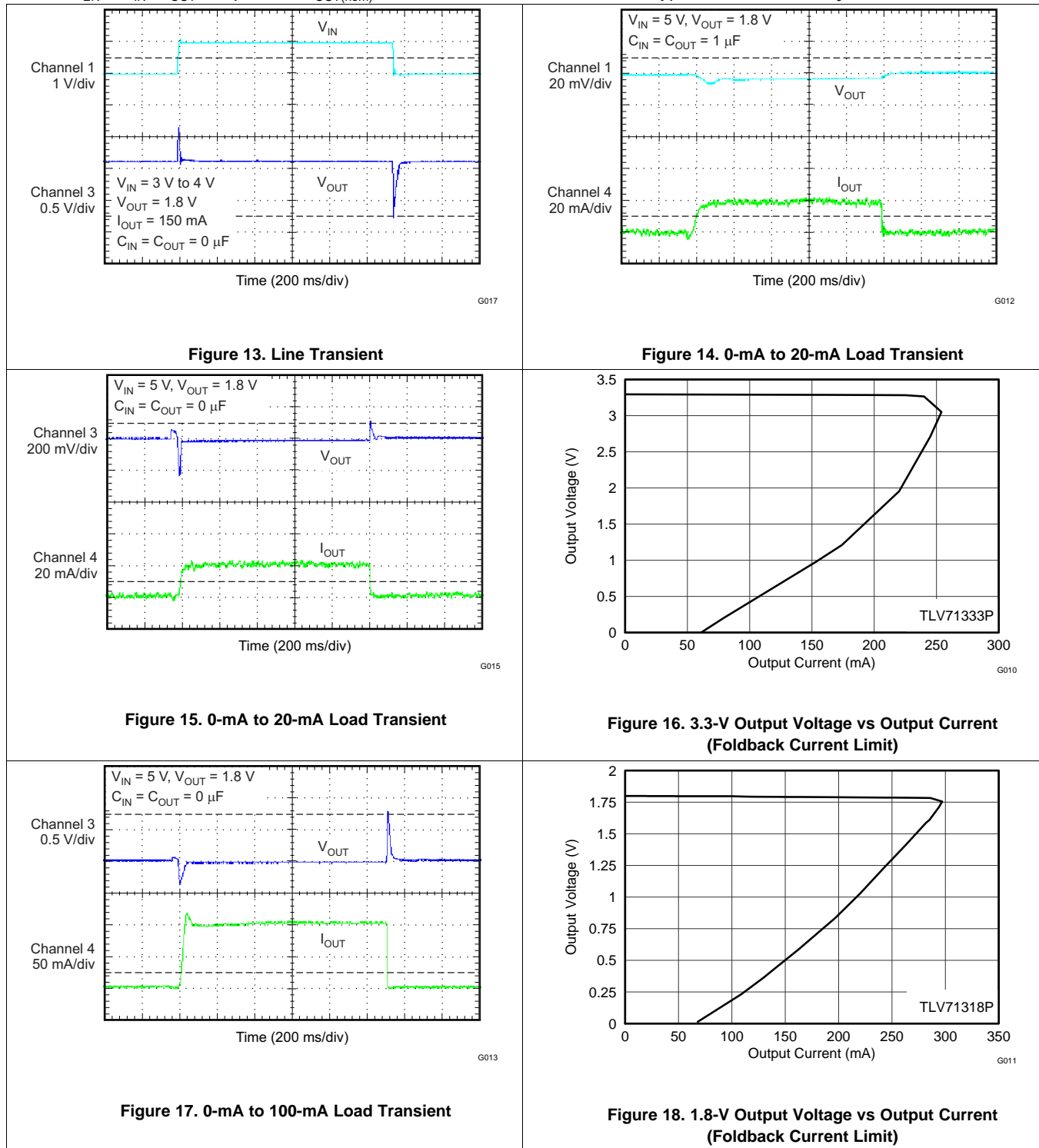


Figure 12. Line Transient

Typical Characteristics (continued)

Over operating temperature range ($T_J = -40^{\circ}\text{C}$ to 125°C), $V_{IN} = V_{OUT(nom)} + 0.5\text{ V}$ or 2.0 V (whichever is greater), $I_{OUT} = 10\text{ mA}$, $V_{EN} = V_{IN}$, $C_{OUT} = 1\text{ }\mu\text{F}$, and $V_{OUT(nom)} = 1.8\text{ V}$, unless otherwise noted. Typical values are at $T_J = 25^{\circ}\text{C}$.



Typical Characteristics (continued)

Over operating temperature range ($T_J = -40^{\circ}\text{C}$ to 125°C), $V_{IN} = V_{OUT(nom)} + 0.5\text{ V}$ or 2.0 V (whichever is greater), $I_{OUT} = 10\text{ mA}$, $V_{EN} = V_{IN}$, $C_{OUT} = 1\text{ }\mu\text{F}$, and $V_{OUT(nom)} = 1.8\text{ V}$, unless otherwise noted. Typical values are at $T_J = 25^{\circ}\text{C}$.

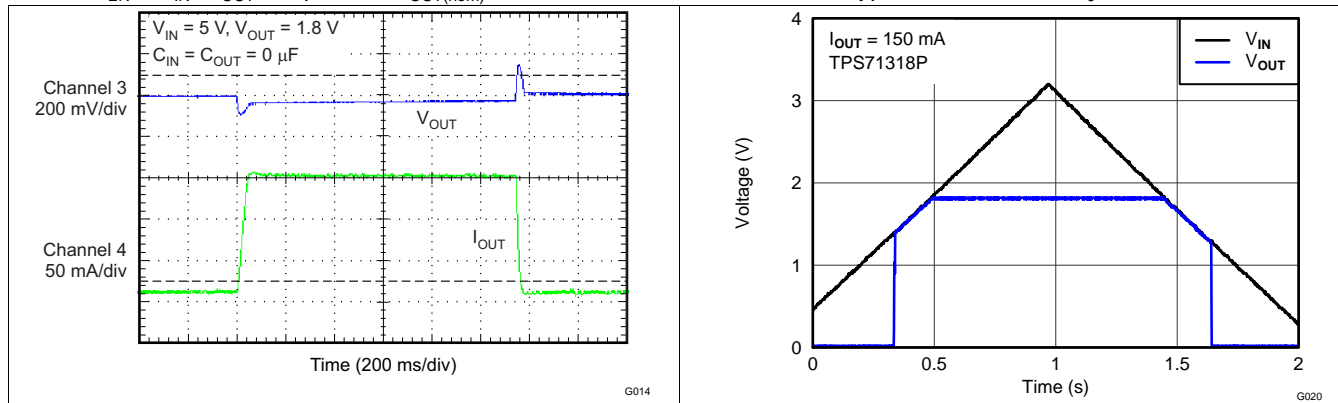


Figure 19. 10-mA to 150-mA Load Transient

Figure 20. V_{IN} Power-Up and Power-Down

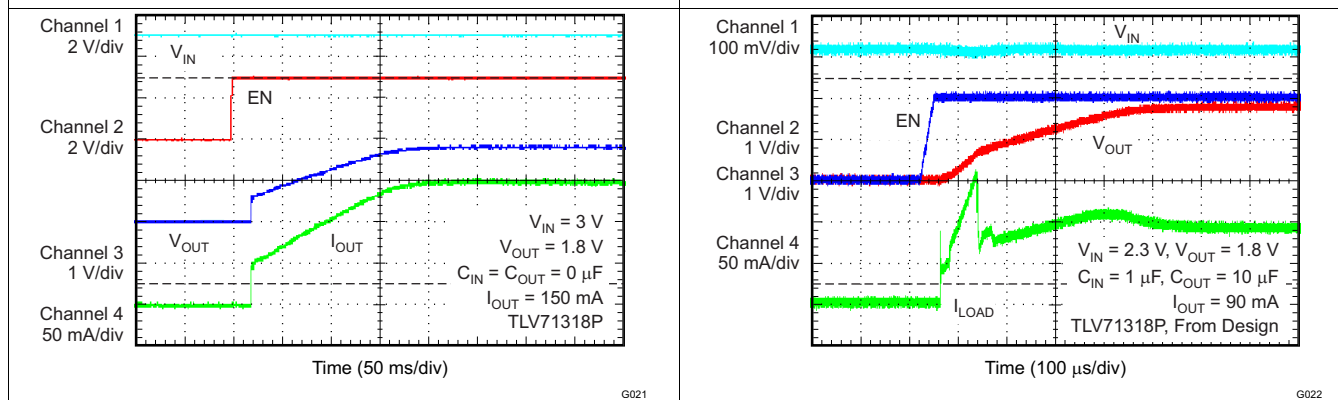


Figure 21. Start-up With EN

Figure 22. Start-up With EN

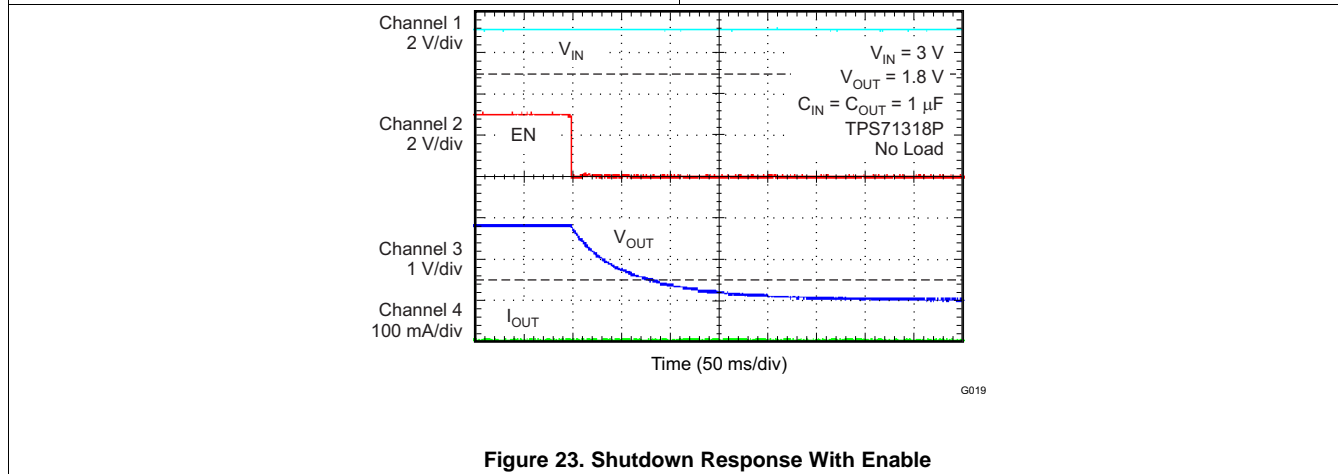


Figure 23. Shutdown Response With Enable

7 Detailed Description

7.1 Overview

These devices belong to a new family of next-generation value low-dropout (LDO) regulators. These devices consume low quiescent current and deliver excellent line and load transient performance. These characteristics, combined with low noise, very good PSRR with little ($V_{IN} - V_{OUT}$) headroom, make this family of devices ideal for RF portable applications.

This family of regulators offers current limit and thermal protection. Device operating junction temperature is -40°C to 125°C .

7.2 Functional Block Diagrams

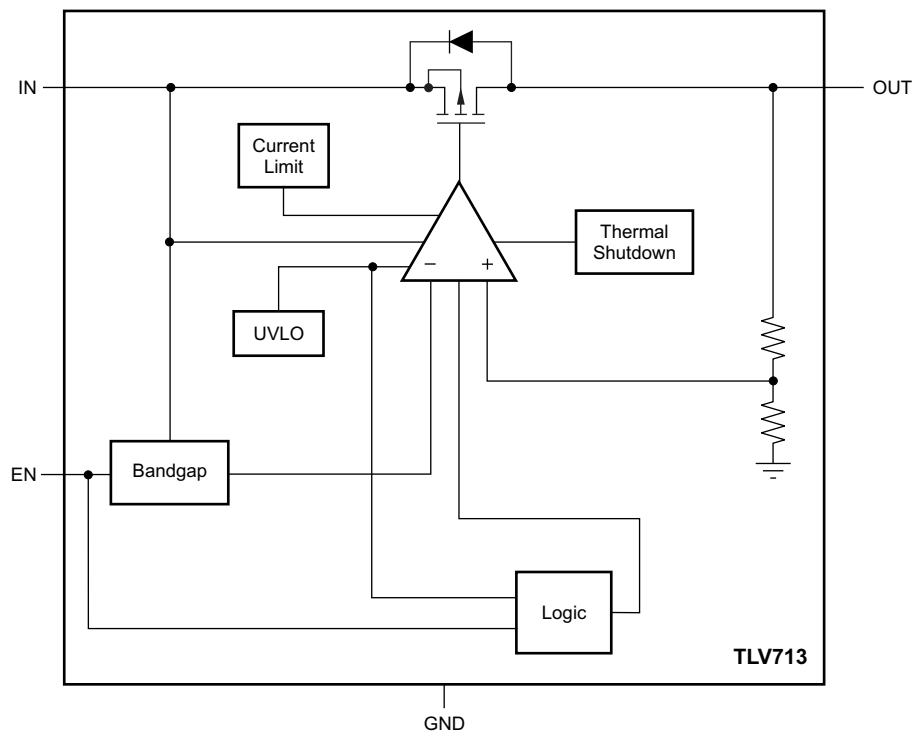


Figure 24. TLV713 Block Diagram

Functional Block Diagrams (continued)

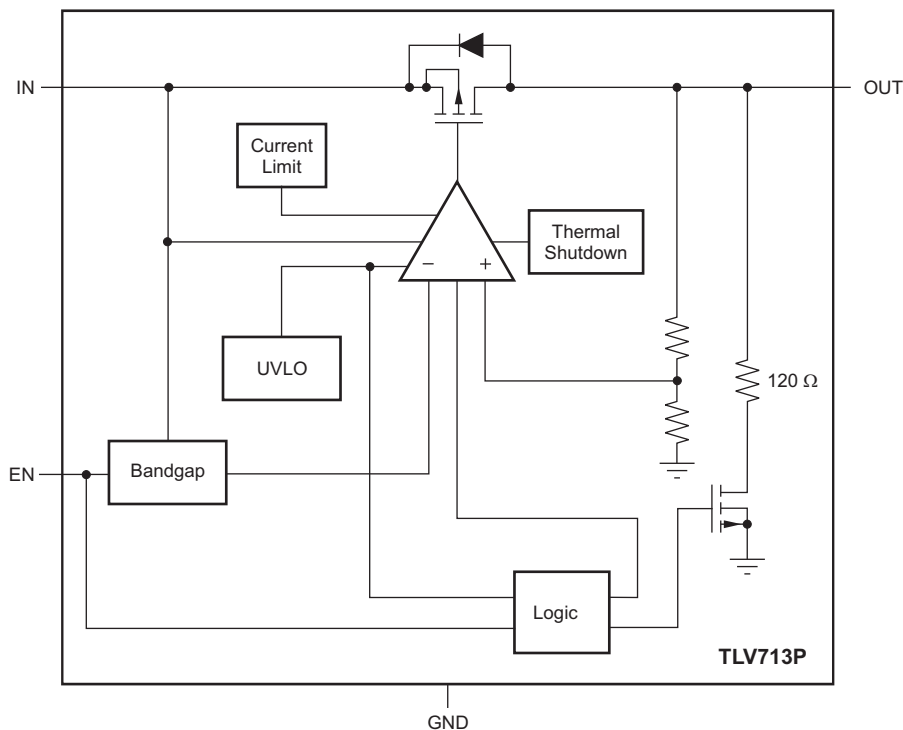


Figure 25. TLV713P Block Diagram

7.3 Feature Description

7.3.1 Undervoltage Lockout (UVLO)

The TLV713 uses a UVLO circuit that disables the output until the input voltage is greater than the rising UVLO voltage. This circuit ensures that the device does not exhibit any unpredictable behavior when the supply voltage is lower than the operational range of the internal circuitry, $V_{IN(min)}$. During UVLO disable, the output of the TLV713P version is connected to ground with a 120-Ω pulldown resistor. Fast rising and falling voltage changes near UVLO levels require at least a 1-ms delay before the rising and falling edges; see the [UVLO Circuit Limitation](#) section.

7.3.2 Shutdown

The enable pin (EN) is active high. Enable the device by forcing the EN pin to exceed $V_{EN(high)}$ (0.9 V, minimum). Turn off the device by forcing the EN pin to drop below 0.4 V. If shutdown capability is not required, connect EN to IN.

The TLV713P has an internal pulldown MOSFET that connects a 120-Ω resistor to ground when the device is disabled. The discharge time after disabling depends on the output capacitance (C_{OUT}) and the load resistance (R_L) in parallel with the 120-Ω pulldown resistor. The time constant is calculated in [Equation 1](#).

$$\tau = \frac{120 \cdot R_L}{120 + R_L} \cdot C_{OUT} \tag{1}$$

Feature Description (continued)

7.3.3 Foldback Current Limit

The TLV713 has an internal foldback current limit that helps protect the regulator during fault conditions. The current supplied by the device is gradually reduced while the output voltage decreases. When the output is shorted, the LDO supplies a typical current of 40 mA. Output voltage is not regulated when the device is in current limit, and is calculated by [Equation 2](#):

$$V_{OUT} = I_{LIMIT} \times R_{LOAD} \quad (2)$$

The PMOS pass transistor dissipates $[(V_{IN} - V_{OUT}) \times I_{LIMIT}]$ until thermal shutdown is triggered and the device turns off. The device is turned on by the internal thermal shutdown circuit during cool down. If the fault condition continues, the device cycles between current limit and thermal shutdown. See the [Thermal Information](#) section for more details.

The TLV713 PMOS pass element has a built-in body diode that conducts current when the voltage at OUT exceeds the voltage at IN. This current is not limited, so if extended reverse voltage operation is anticipated, external limiting to 5% of the rated output current is recommended.

7.3.4 Thermal Protection

Thermal protection disables the output when the junction temperature rises to approximately 158°C, allowing the device to cool. When the junction temperature cools to approximately 140°C, the output circuitry is again enabled. Depending on power dissipation, thermal resistance, and ambient temperature, the thermal protection circuit may cycle on and off. This cycling limits regulator dissipation, protecting the device from damage as a result of overheating.

Any tendency to activate the thermal protection circuit indicates excessive power dissipation or an inadequate heatsink. For reliable operation, junction temperature must be limited to 125°C maximum. To estimate the margin of safety in a complete design (including heatsink), increase the ambient temperature until the thermal protection is triggered; use worst-case loads and signal conditions.

The TLV713 internal protection circuitry is designed to protect against overload conditions. This circuitry is not intended to replace proper heatsinking. Continuously running the TLV713 into thermal shutdown degrades device reliability.

7.4 Device Functional Modes

7.4.1 Normal Operation

The device regulates to the nominal output voltage under the following conditions:

- The input voltage is at least as high as $V_{IN(min)}$.
- The input voltage is greater than the nominal output voltage added to the dropout voltage.
- The enable voltage has previously exceeded the enable rising threshold voltage and has not decreased below the enable falling threshold.
- The output current is less than the current limit.
- The device junction temperature is less than the maximum specified junction temperature.

7.4.2 Dropout Operation

If the input voltage is lower than the nominal output voltage plus the specified dropout voltage, but all other conditions are met for normal operation, the device operates in dropout mode. In this mode of operation, the output voltage is the same as the input voltage minus the dropout voltage. The transient performance of the device is significantly degraded because the pass device is in the linear region and no longer controls the current through the LDO. Line or load transients in dropout can result in large output voltage deviations.

7.4.3 Disabled

The device is disabled under the following conditions:

- The enable voltage is less than the enable falling threshold voltage or has not yet exceeded the enable rising threshold.
- The device junction temperature is greater than the thermal shutdown temperature.

Table 1 shows the conditions that lead to the different modes of operation.

Table 1. Device Functional Mode Comparison

OPERATING MODE	PARAMETER			
	V_{IN}	V_{EN}	I_{OUT}	T_J
Normal mode	$V_{IN} > V_{OUT(nom)} + V_{DO}$ and $V_{IN} > V_{IN(min)}$	$V_{EN} > V_{EN(high)}$	$I_{OUT} < I_{LIM}$	$T_J < 125^{\circ}C$
Dropout mode	$V_{IN(min)} < V_{IN} < V_{OUT(nom)} + V_{DO}$	$V_{EN} > V_{EN(high)}$	—	$T_J < 125^{\circ}C$
Disabled mode (any true condition disables the device)	—	$V_{EN} < V_{EN(low)}$	—	$T_J > 158^{\circ}C$

8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

8.1.1 Input and Output Capacitor Considerations

The TLV713 uses an advanced internal control loop to obtain stable operation both with and without the use of input or output capacitors. The TLV713 dynamic performance is improved with the use of an output capacitor. An output capacitance of 0.1 μF or larger generally provides good dynamic response. X5R- and X7R-type ceramic capacitors are recommended because these capacitors have minimal variation in value and equivalent series resistance (ESR) over temperature.

Although an input capacitor is not required for stability, it is good analog design practice to connect a 0.1- μF to 1- μF capacitor from IN to GND. This capacitor counteracts reactive input sources and improves transient response, input ripple, and PSRR. An input capacitor is recommended if the source impedance is more than 0.5 Ω . A higher-value capacitor may be necessary if large, fast, rise-time load transients are anticipated or if the device is located several inches from the input power source.

8.1.2 Dropout Voltage

The TLV713 uses a PMOS pass transistor to achieve low dropout. When $(V_{\text{IN}} - V_{\text{OUT}})$ is less than the dropout voltage (V_{DO}), the PMOS pass device is in the linear region of operation and the input-to-output resistance is the $R_{\text{DS(on)}}$ of the PMOS pass element. V_{DO} scales approximately with output current because the PMOS device behaves like a resistor in dropout. As with any linear regulator, PSRR and transient response are degraded as $(V_{\text{IN}} - V_{\text{OUT}})$ approaches dropout.

8.1.3 Transient Response

As with any regulator, increasing the size of the output capacitor reduces over- and undershoot magnitude but increases the duration of the transient response.

8.1.4 UVLO Circuit Limitation

The TLV713 UVLO circuit is sensitive to fast rising and falling input voltage changes that result in the device turning on and off. When the input voltage drops below the minimum V_{IN} and the device is turned off, provide a minimum 1-ms delay before turning on the device again. This minimum 1-ms delay allows the internal circuit to reset to the correct state. If the TLV713 is turned on again before the delay elapses, an EN toggle is required for the internal circuit to reset to the correct state.

8.2 Typical Application

Several versions of the TPS713 are ideal for powering the [MSP430 microcontroller](#).

[Figure 26](#) shows a diagram of the TLV713 powering an MSP430 microcontroller. [Table 2](#) shows potential applications of some voltage versions.

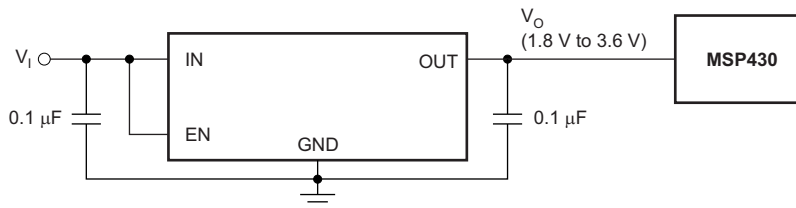


Figure 26. TLV713 Powering a Microcontroller

Table 2. Typical MSP430 Applications

DEVICE	V _{OUT} (Typ)	APPLICATION
TLV71318P	1.8 V	Allows for lowest power consumption with many MSP430s
TLV71325P	2.5 V	2.2-V supply required by many MSP430s for flash programming and erasing

8.2.1 Design Requirements

[Table 3](#) lists the design requirements.

Table 3. Design Parameters

PARAMETER	DESIGN REQUIREMENT
Input voltage	4.2 V to 3 V (Lithium Ion battery)
Output voltage	1.8 V, ±1%
DC output current	10 mA
Peak output current	75 mA
Maximum ambient temperature	65°C

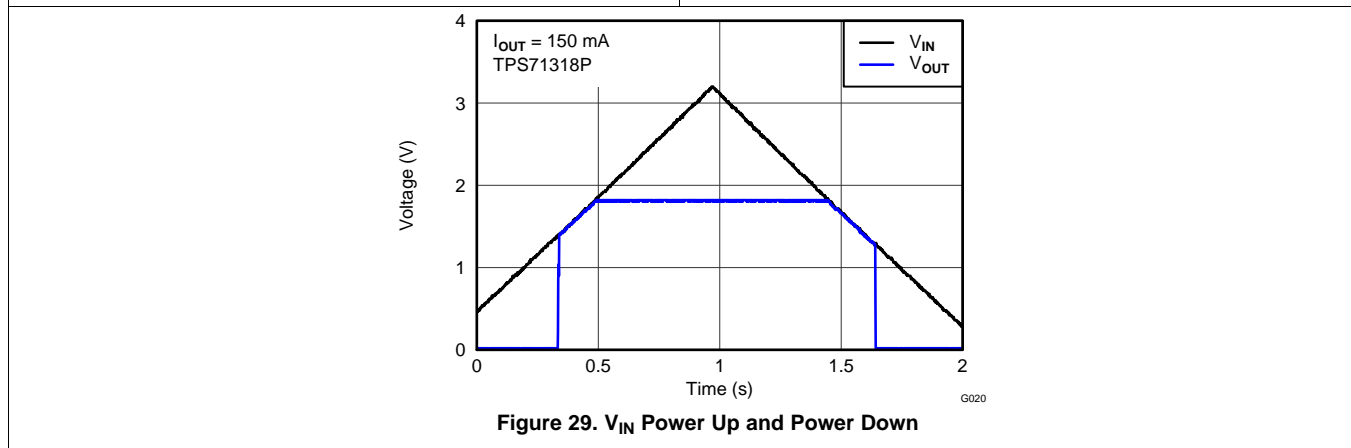
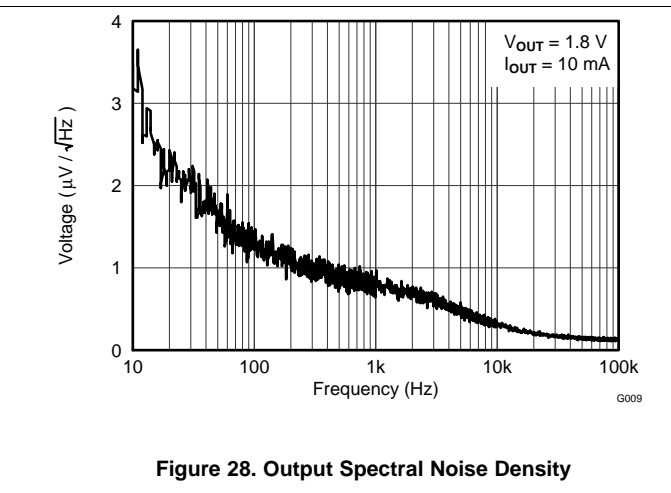
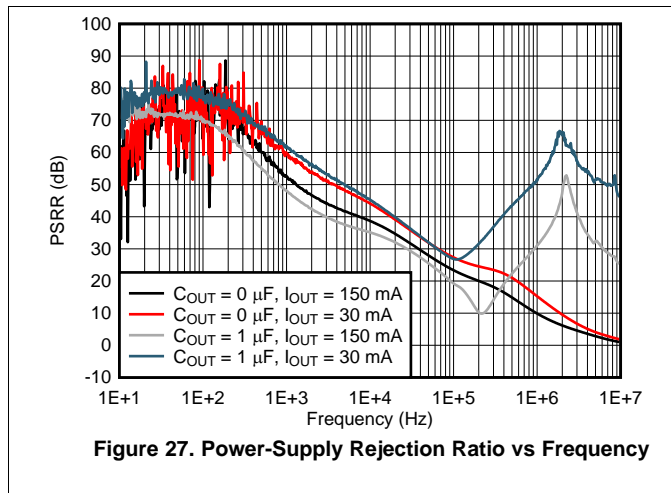
8.2.2 Detailed Design Procedure

An input capacitor is not required for this design because of the low impedance connection directly to the battery.

No output capacitor allows for the minimal possible inrush current during start-up, ensuring the 180-mA maximum input current limit is not exceeded.

Verify that the maximum junction temperature is not exceeded by referring to [Figure 30](#).

8.2.3 Application Curves



8.3 What to Do and What Not to Do

Place at least one 0.1- μ F ceramic capacitor as close as possible to the OUT pin of the regulator for best transient performance.

Place at least one 1- μ F capacitor as close as possible to the IN pin for best transient performance.

Do not place the output capacitor more than 10 mm away from the regulator.

Do not exceed the absolute maximum ratings.

Do not continuously operate the device in current limit or near thermal shutdown.

9 Power Supply Recommendations

These devices are designed to operate from an input voltage supply range from 1.4 V to 5.5 V. The input voltage range must provide adequate headroom for the device to have a regulated output. This input supply must be well-regulated and stable. If the input supply is noisy, additional input capacitors with low ESR can help improve the output noise performance.

10 Layout

10.1 Layout Guidelines

10.1.1 Board Layout Recommendations to Improve PSRR and Noise Performance

Input and output capacitors must be placed as close to the device pins as possible. To improve AC performance (such as PSRR, output noise, and transient response), TI recommends that the board be designed with separate ground planes for V_{IN} and V_{OUT} , with the ground plane connected only at the device GND pin. In addition, the output capacitor ground connection must be connected directly to the device GND pin. High-ESR capacitors may degrade PSRR performance.

10.1.2 Power Dissipation

The ability to remove heat from the die is different for each package type, presenting different considerations in the printed-circuit-board (PCB) layout. The PCB area around the device that is free of other components moves the heat from the device to the ambient air. Performance data for JEDEC low- and high-K boards are given in [Thermal Information](#). Using heavier copper increases the effectiveness in removing heat from the device. The addition of plated through-holes to heat-dissipating layers also improves the heatsink effectiveness.

Power dissipation depends on input voltage and load conditions. Power dissipation (P_D) can be approximated by the product of the output current times the voltage drop across the output pass element (V_{IN} to V_{OUT}), as shown in [Equation 3](#).

$$P_D = (V_{IN} - V_{OUT}) \times I_{OUT} \quad (3)$$

[Figure 30](#) shows the maximum ambient temperature versus the power dissipation of the TLV713. This figure assumes the device is soldered on a JEDEC standard, high-K layout with no airflow over the board. Actual board thermal impedances vary widely. If the application requires high power dissipation, having a thorough understanding of the board temperature and thermal impedances is helpful to ensure the TLV713 does not operate above a junction temperature of 125°C.

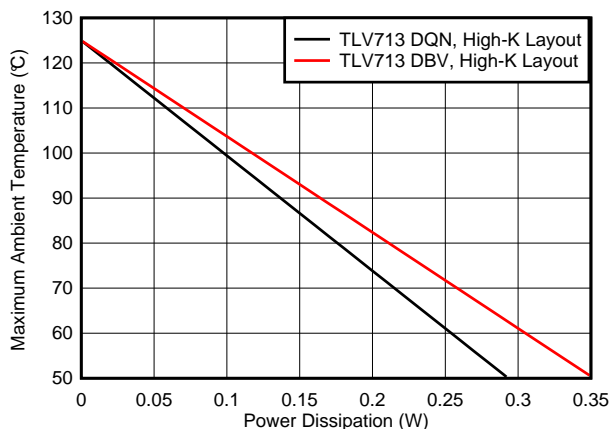


Figure 30. Maximum Ambient Temperature vs Device Power Dissipation

Estimating the junction temperature can be done by using the thermal metrics Ψ_{JT} and Ψ_{JB} , shown in the [Thermal Information](#) table. These metrics are a more accurate representation of the heat transfer characteristics of the die and the package than $R_{\theta JA}$. The junction temperature can be estimated with [Equation 4](#).

Layout Guidelines (continued)

$$\Psi_{JT}: T_J = T_T + \Psi_{JT} \cdot P_D$$

$$\Psi_{JB}: T_J = T_B + \Psi_{JB} \cdot P_D$$

where

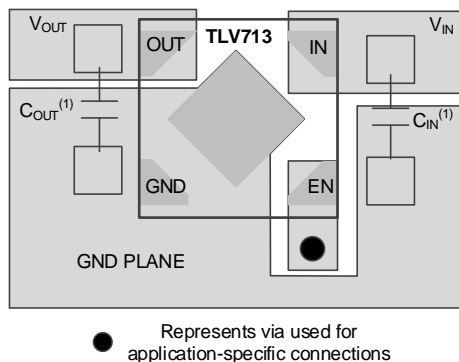
- P_D is the power dissipation shown by Equation 3,
 - T_T is the temperature at the center-top of the IC package,
 - T_B is the PCB temperature measured 1 mm away from the IC package on the PCB surface.
- (4)

NOTE

Both T_T and T_B can be measured on actual application boards using a thermo-gun (an infrared thermometer).

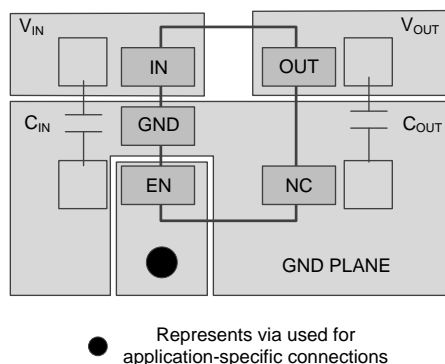
For more information about measuring T_T and T_B , see the [Using New Thermal Metrics application note](#), available for download at www.ti.com.

10.2 Layout Examples



(1) Not required.

Figure 31. X2SON Layout Example



(1) Not required.

Figure 32. SOT-23 Layout Example

11 デバイスおよびドキュメントのサポート

11.1 デバイス・サポート

11.1.1 開発サポート

11.1.1.1 評価基板

TLV713 を使用する回路の性能の初期評価に役立てるため、3 つの評価基板 (EVM) を提供しています。

- [TLV71312PEVM-171](#)
- [TLV71318PEVM-171](#)
- [TLV71333PEVM-171](#)

これらの EVM はテキサス・インスツルメンツの Web サイトのデバイス製品フォルダから請求、または [TI eStore](#) から直接お求めになれます。

11.1.1.2 SPICEモデル

SPICEを使用した回路パフォーマンスのコンピュータによるシミュレーションは、アナログ回路やシステムのパフォーマンスを分析するため多くの場合に有用です。TLV713 用の SPICE モデルは、製品フォルダの「ツールとソフトウェア」から入手できます。

11.1.2 デバイスの項目表記

表 4. 注文情報⁽¹⁾⁽²⁾

製品名	V_o
TLV713xx(x)Pyyyz	<p>xx(x) は公称出力電圧です。出力電圧の分解能が 100mV の場合、注文番号に 2 桁が使用されます。それ以外の場合は 3 桁が使用されます (例: 28 = 2.8V、475 = 4.75V)。</p> <p>P はオプションです。P の付いたデバイスは、アクティブ出力放電機能付きの LDO レギュレータを備えています。</p> <p>YYY はパッケージ指定子です。</p> <p>Z はパッケージ数量です。R はリール (3000 ピース)、T はテープ (250 ピース) を表します。</p>

(1) 最新のパッケージと発注情報については、このデータシートの末尾にある「パッケージ・オプション」の付録を参照するか、www.ti.com にあるデバイスの製品フォルダをご覧ください。

(2) 出力電圧は、1.0V から 3.3V まで、50mV 刻みで利用できます。詳細と在庫については、工場にお問い合わせください。

11.2 ドキュメントのサポート

11.2.1 関連資料

関連資料については、以下を参照してください。

- テキサス・インスツルメンツ、[『新しい熱評価基準の解説』アプリケーション・レポート](#)
- テキサス・インスツルメンツ、[『TLV713xxPEVM-171 評価基板』ユーザー・ガイド](#)

11.3 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.com のデバイス製品フォルダを開いてください。右上の「アラートを受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

11.4 コミュニティ・リソース

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

11.5 商標

E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

11.6 静電気放電に関する注意事項



すべての集積回路は、適切なESD保護方法を用いて、取扱いと保存を行うようにして下さい。

静電気放電はわずかな性能の低下から完全なデバイスの故障に至るまで、様々な損傷を与えます。高精度の集積回路は、損傷に対して敏感であり、極めてわずかなパラメータの変化により、デバイスに規定された仕様に適合しなくなる場合があります。

11.7 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TLV71310PDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VUQI	Samples
TLV71310PDBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VUQI	Samples
TLV71310PDQNR	ACTIVE	X2SON	DQN	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	ET	Samples
TLV71310PDQNT	ACTIVE	X2SON	DQN	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	ET	Samples
TLV71311PDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VUPI	Samples
TLV71311PDBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VUPI	Samples
TLV71312PDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VUEI	Samples
TLV71312PDBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VUEI	Samples
TLV71312PDQNR	ACTIVE	X2SON	DQN	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AF	Samples
TLV71312PDQNT	ACTIVE	X2SON	DQN	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AF	Samples
TLV71315PDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VUGI	Samples
TLV71315PDBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VUGI	Samples
TLV71315PDQNR	ACTIVE	X2SON	DQN	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AY	Samples
TLV71315PDQNT	ACTIVE	X2SON	DQN	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AY	Samples
TLV713185PDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VUII	Samples
TLV713185PDBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VUII	Samples
TLV713185PDQNR	ACTIVE	X2SON	DQN	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	A1	Samples
TLV713185PDQNT	ACTIVE	X2SON	DQN	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	A1	Samples
TLV71318PDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VUDI	Samples
TLV71318PDBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VUDI	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TLV71318PDQNR	ACTIVE	X2SON	DQN	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AW	Samples
TLV71318PDQNT	ACTIVE	X2SON	DQN	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AW	Samples
TLV71320DQNR	ACTIVE	X2SON	DQN	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	B2	Samples
TLV71320DQNT	ACTIVE	X2SON	DQN	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	B2	Samples
TLV71325PDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VUJI	Samples
TLV71325PDBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VUJI	Samples
TLV71325PDQNR	ACTIVE	X2SON	DQN	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AZ	Samples
TLV71325PDQNT	ACTIVE	X2SON	DQN	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AZ	Samples
TLV713285PDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VULI	Samples
TLV713285PDBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VULI	Samples
TLV713285PDQNR	ACTIVE	X2SON	DQN	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	A2	Samples
TLV713285PDQNT	ACTIVE	X2SON	DQN	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	A2	Samples
TLV71328PDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VUKI	Samples
TLV71328PDBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VUKI	Samples
TLV71328PDQNR	ACTIVE	X2SON	DQN	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AK	Samples
TLV71328PDQNT	ACTIVE	X2SON	DQN	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AK	Samples
TLV71330PDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VUMI	Samples
TLV71330PDBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VUMI	Samples
TLV71330PDQNR	ACTIVE	X2SON	DQN	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AL	Samples
TLV71330PDQNT	ACTIVE	X2SON	DQN	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AL	Samples
TLV71333PDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VUFI	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TLV71333PDBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VUFI	Samples
TLV71333PDQNR	ACTIVE	X2SON	DQN	4	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AH	Samples
TLV71333PDQNT	ACTIVE	X2SON	DQN	4	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AH	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF TLV713P :

- Automotive : [TLV713P-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV71310PDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV71310PDBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV71310PDQNR	X2SON	DQN	4	3000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV71310PDQNT	X2SON	DQN	4	250	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV71311PDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV71311PDBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV71312PDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV71312PDBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV71312PDQNR	X2SON	DQN	4	3000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV71312PDQNT	X2SON	DQN	4	250	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV71315PDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV71315PDBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV71315PDQNR	X2SON	DQN	4	3000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV71315PDQNT	X2SON	DQN	4	250	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV713185PDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV713185PDBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV713185PDQNR	X2SON	DQN	4	3000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV713185PDQNT	X2SON	DQN	4	250	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV71318PDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV71318PDBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV71318PDQNR	X2SON	DQN	4	3000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV71318PDQNT	X2SON	DQN	4	250	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV71320DQNR	X2SON	DQN	4	3000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV71320DQNT	X2SON	DQN	4	250	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV71325PDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV71325PDBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV71325PDQNR	X2SON	DQN	4	3000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV71325PDQNT	X2SON	DQN	4	250	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV713285PDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV713285PDBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV713285PDQNR	X2SON	DQN	4	3000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV713285PDQNT	X2SON	DQN	4	250	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV71328PDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV71328PDBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV71328PDQNR	X2SON	DQN	4	3000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV71328PDQNT	X2SON	DQN	4	250	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV71330PDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV71330PDBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV71330PDQNR	X2SON	DQN	4	3000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV71330PDQNT	X2SON	DQN	4	250	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV71333PDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV71333PDBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV71333PDQNR	X2SON	DQN	4	3000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV71333PDQNT	X2SON	DQN	4	250	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV71310PDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TLV71310PDBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
TLV71310PDQNR	X2SON	DQN	4	3000	210.0	185.0	35.0
TLV71310PDQNT	X2SON	DQN	4	250	210.0	185.0	35.0
TLV71311PDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TLV71311PDBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
TLV71312PDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TLV71312PDBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
TLV71312PDQNR	X2SON	DQN	4	3000	210.0	185.0	35.0
TLV71312PDQNT	X2SON	DQN	4	250	210.0	185.0	35.0
TLV71315PDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TLV71315PDBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
TLV71315PDQNR	X2SON	DQN	4	3000	210.0	185.0	35.0
TLV71315PDQNT	X2SON	DQN	4	250	210.0	185.0	35.0
TLV713185PDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TLV713185PDBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
TLV713185PDQNR	X2SON	DQN	4	3000	210.0	185.0	35.0
TLV713185PDQNT	X2SON	DQN	4	250	210.0	185.0	35.0

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV71318PDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TLV71318PDBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
TLV71318PDQNR	X2SON	DQN	4	3000	210.0	185.0	35.0
TLV71318PDQNT	X2SON	DQN	4	250	210.0	185.0	35.0
TLV71320DQNR	X2SON	DQN	4	3000	210.0	185.0	35.0
TLV71320DQNT	X2SON	DQN	4	250	210.0	185.0	35.0
TLV71325PDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TLV71325PDBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
TLV71325PDQNR	X2SON	DQN	4	3000	210.0	185.0	35.0
TLV71325PDQNT	X2SON	DQN	4	250	210.0	185.0	35.0
TLV713285PDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TLV713285PDBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
TLV713285PDQNR	X2SON	DQN	4	3000	210.0	185.0	35.0
TLV713285PDQNT	X2SON	DQN	4	250	210.0	185.0	35.0
TLV71328PDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TLV71328PDBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
TLV71328PDQNR	X2SON	DQN	4	3000	210.0	185.0	35.0
TLV71328PDQNT	X2SON	DQN	4	250	210.0	185.0	35.0
TLV71330PDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TLV71330PDBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
TLV71330PDQNR	X2SON	DQN	4	3000	210.0	185.0	35.0
TLV71330PDQNT	X2SON	DQN	4	250	210.0	185.0	35.0
TLV71333PDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TLV71333PDBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
TLV71333PDQNR	X2SON	DQN	4	3000	210.0	185.0	35.0
TLV71333PDQNT	X2SON	DQN	4	250	210.0	185.0	35.0

DBV0005A



PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-178.
4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
5. Support pin may differ or may not be present.

4214839/J 02/2024

EXAMPLE BOARD LAYOUT

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

4214839/J 02/2024

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214839/J 02/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

GENERIC PACKAGE VIEW

DQN 4

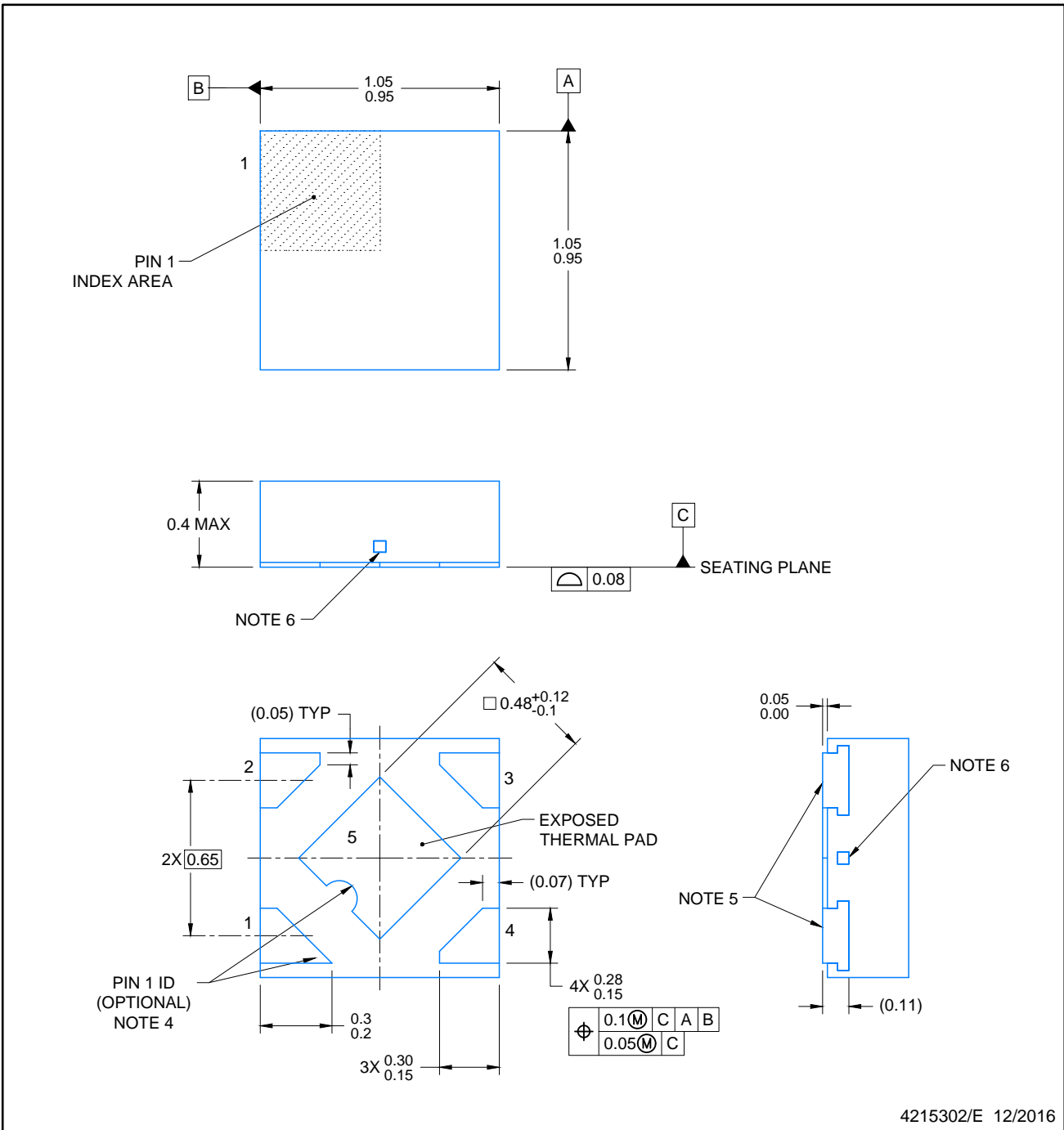
X2SON - 0.4 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4210367/F



4215302/E 12/2016

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.
4. Features may not exist. Recommend use of pin 1 marking on top of package for orientation purposes.
5. Shape of exposed side leads may differ.
6. Number and location of exposed tie bars may vary.



LAND PATTERN EXAMPLE
SCALE: 40X



SOLDER MASK DETAIL

4215302/E 12/2016

NOTES: (continued)

7. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).
8. If any vias are implemented, it is recommended that vias under paste be filled, plugged or tented.



SOLDER PASTE EXAMPLE
 BASED ON 0.075 - 0.1mm THICK STENCIL
 EXPOSED PAD
 88% PRINTED SOLDER COVERAGE BY AREA
 SCALE: 60X

4215302/E 12/2016

NOTES: (continued)

- 9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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